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List of Publications by Year in descending order

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20
papers

4,540
citations

623734

14
h-index

839539

18
g-index

20
all docs

20
docs citations

20
times ranked

1850
citing authors

#	ARTICLE	IF	CITATIONS
1	Quantum Confinement Effects in Capacitance Behavior of Multigate Silicon Nanowire MOSFETs. IEEE Nanotechnology Magazine, 2011, 10, 300-309.	2.0	20
2	Nanowire to Single-Electron Transistor Transition in Trigate SOI MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 26-32.	3.0	9
3	Influence of Elastic and Inelastic Electron-Phonon Interaction on Quantum Transport in Multigate Silicon Nanowire MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 1029-1037.	3.0	9
4	Junctionless Multiple-Gate Transistors for Analog Applications. IEEE Transactions on Electron Devices, 2011, 58, 2511-2519.	3.0	234
5	Investigation of high-performance sub-50nm junctionless nanowire transistors. Microelectronics Reliability, 2011, 51, 1166-1171.	1.7	32
6	Performance estimation of junctionless multigate transistors. Solid-State Electronics, 2010, 54, 97-103.	1.4	487
7	Nanowire transistors without junctions. Nature Nanotechnology, 2010, 5, 225-229.	31.5	1,993
8	Effect of intravalley acoustic phonon scattering on quantum transport in multigate silicon nanowire metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2010, 108, 034510.	2.5	19
9	Reduced electric field in junctionless transistors. Applied Physics Letters, 2010, 96, 073510.	3.3	269
10	Mobility improvement in nanowire junctionless transistors by uniaxial strain. Applied Physics Letters, 2010, 97, .	3.3	38
11	Low subthreshold slope in junctionless multigate transistors. Applied Physics Letters, 2010, 96, .	3.3	195
12	High-Temperature Performance of Silicon Junctionless MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 620-625.	3.0	359
13	Nanowire zero-capacitor DRAM transistors with and without junctions. , 2010, , .		17
14	Dissipative transport in Multigate silicon nanowire transistors. , 2010, , .		4
15	A new F(ast)-CMS NEGF algorithm for efficient 3D simulations of switching characteristics enhancement in constricted tunnel barrier silicon nanowire MuGFETs. Journal of Computational Electronics, 2009, 8, 287-306.	2.5	31
16	Comparison of different surface orientation in narrow fin MuGFETs. Microelectronic Engineering, 2009, 86, 2381-2384.	2.4	5
17	Analytical model for the high-temperature behaviour of the subthreshold slope in MuGFETs. Microelectronic Engineering, 2009, 86, 2067-2071.	2.4	3
18	Junctionless multigate field-effect transistor. Applied Physics Letters, 2009, 94, .	3.3	768

#	ARTICLE	IF	CITATIONS
19	Comparison of contact resistance between accumulation-mode and inversion-mode multigate FETs. Solid-State Electronics, 2008, 52, 1815-1820.	1.4	16
20	Sensitivity of trigate MOSFETs to random dopant induced threshold voltage fluctuations. Solid-State Electronics, 2008, 52, 1872-1876.	1.4	32